

AMENDMENTS TO THE SPECIFICATION

Please replace Paragraph [0079] with the following paragraph rewritten in amendment format:

[0079] However, when a precursor containing an amino functional group such as TEMAH is used to form the HfO₂ layer, nitrogen can be included in the resulting thin film without implementing a subsequent heat treatment. For example, it has been reported that an HfO₂ thin film formed using a LPCVD method using ~~TEDAH~~ TDEAH [Hf(N(C₂H₅)₂)₄] and O₂, contains about 7% nitrogen.